

Remarks/Arguments

Examiner Steven Ho Yin Loke is thanked for the thorough Search and Examination of the Subject Application for Patent. Examiner Loke is also thanked for finding Claims 1-9 and 11-26 potentially allowable. Examiner Loke is also thanked for suggestions regarding rewriting some of the claims.

The Specification has been amended at page 7, line 12 to correct a typographical error by replacing "well12" with -- well 12 --. A space was inadvertently omitted between well and 12.

Claim 1 has been amended to replace "accumulating charge at the PN junction between said P well and said N well during a charge integration period, wherein said charge integration period follows said reset period" with -- accumulating charge at the PN junction between said P type silicon substrate and said N well during a charge integration period, thereby changing the potential of said N well, said P well, and said floating gate and wherein said charge integration period follows said reset period --.

Claim 8 has been amended to replace "accumulating charge at the PN junction between said N well and said P well during a charge integration period, wherein said charge integration period follows said reset period" with -- accumulating charge at the PN junction between said N type silicon substrate and said P well during a charge integration period, thereby changing the potential of said P well, said N well, and said floating gate and wherein said charge integration period follows said reset period --. The basis for

these amendments to Claims 1 and 8 can be found in the Specification from page 8, line 14 to page 9, line 7 and page 10, lines 1-8.

Claims 2, 4, and 17 have been amended to change "said P well" to -- said P type silicon substrate --. Claims 9, 11, and 23 has been amended to change "said N well" to -- said N type silicon substrate --. The basis for these amendments to Claims 2, 4, 9, 11, 17, and 23 can be found in the Specification from page 8, line 14 to page 9, line 7 and page 10, lines 1-8.

Claims 1, 8, 15, and 21 have been amended to change "wherein said the thickness of said gate oxide is sufficiently small" with -- wherein said gate oxide has a thickness which is sufficiently small -- to correct an antecedent basis problem.

Claims 14 and 15 have been amended to change "said determining the potential" to -- said reading the potential -- to correct an antecedent basis problem. Claim 26 has been amended to change "said reading the potential" to -- said determining the potential -- to correct an antecedent basis problem.

Claims 13 and 25 have been amended to change "said P well" to -- said N well --. The basis for this change to Claims 13 and 25 can be found in the Specification from page 8, line 14 to page 9, line 7 and page 10, lines 1-8.

Claim 7 and 14 and the last clause of Claims 1, 8, and 21 have been amended to change "gate" to -- floating gate -- for consistency within Claims 1, 8, and 21; for consistency between Claim 1 and Claim 7, which depends from Claim 1; and for consistency between Claim 8 and Claim 14, which depends from Claim 8..

Claim 10 has been amended to change "said P well" to -- said N well -- and to change "electrical connection between said floating gate and" to -- forming an electrical connection between said floating gate and -- to make Claim 10 consistent with Claim 8, from which Claim 10 depends, and to make Claim 10 read properly as a method claim. The basis for these changes to Claim 10 can be found in the Specification from page 8, line 14 to page 9, line 7 and page 10, lines 1-8.

All occurrences of "gate" in the claims have been changed to -- floating gate -- to improve the clarity of the claims. Occurrences of "floating gate" or "gate oxide" have not been changed.

Figs. 1 and 4 of the Drawings have been amended to extend the lead line for Reference Number 15 to the boundary between the region identified by Reference Number 12 and the region identified by Reference Number 14. The basis for these changes to Figs. 1 and 4 can be found in the Specification on page 7, lines 11-21 and in Fig. 2 of the Drawings. Replacement Drawings containing these amendments to Figs. 1 and 4 are attached to this paper.

Reconsideration of the Objection to the Disclosure is requested. The written description on page 7, line 13 showing the PN junction 15 is formed between the P well 14 and the N well 12 is correct. However the lead line from Reference Number 15 in Figs. 1 and 4 of the Drawings directing Reference Number 15 to the Junction between region 12 and the substrate 10 is not correct. The lead line should have directed Reference Number 15 to the junction between region 14 and region 12. The lead line directing Reference Number 15 to the junction between region 14 and region 12 is correct in Fig. 2. The Drawings have been amended to correct this error and Replacement Drawings containing these amendments to Figs. 1 and 4 are attached to this paper. The Specification has been amended at page 7, line 12 to correct a typographical error by replacing "well12" with -- well 12 --. A space was inadvertently omitted between well and 12.

Reconsideration of the Objection to Claims 1-26 is requested. In Claims 1, 8, 15, and 21, line 8, the phrase "wherein said the thickness of said gate oxide is sufficiently small" has been changed to -- wherein said gate oxide has a thickness which is sufficiently small -- to correct a problem with antecedent basis and to improve the clarity of the claims. In Claim 13, lines 1-2 the phrase "said resetting the potential between said P well and said substrate" has been changed to -- said resetting the potential between said N well and said substrate -- to correct a problem with antecedent basis and to improve the clarity of the claim. In Claim 14 the phrase "determining the potential of said gate" has been changed to -- reading the potential of said floating gate -- to correct a problem with antecedent basis and to improve the clarity of the claim. In Claim 15, lines

14-15, the phrase "said means for determining the potential of said floating gate" has been changed to -- said means for reading the potential of said floating gate -- to correct a problem with antecedent basis. In Claim 25, lines 1-2, the phrase "said means for resetting the potential between said P well and said substrate" has been changed to -- said means for resetting the potential between said N well and said substrate -- to correct a problem with antecedent basis. In Claim 26, lines 1-2, the phrase "said means for reading the potential of said gate" has been changed to -- said means for determining the potential of said floating gate -- to correct a problem with antecedent basis and to improve the clarity of the claim.

Reconsideration of the Rejection of Claim 10 under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention is requested. Claim 10 has been amended to change "said P well" to -- said N well -- and to change "electrical connection between said floating gate and" to -- forming an electrical connection between said floating gate and --. With these changes to Claim 10 the first phrase of Claim 10 reads as suggested by the Examiner. The second phrase of Claim 10 has been amended to read properly as a phrase of a method claim. It is believed that Claim 10, as amended, meets the requirements of 35 U.S.C. 112, second paragraph.

It is believed that Claims 1-9 and 11-26 have been rewritten to overcome the objections set forth in this Office Action; that Claim 10 has been rewritten to meet the requirements of 35 U.S.C. 112, second paragraph; and that Claims 1-26, as amended, should now be allowable.

It is requested that should Examiner Loke not find that the Claims are now Allowable that the Examiner call the undersigned Agent at (845)-462-5363 to overcome any problems preventing allowance.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "Larry J. Prescott".

Larry J. Prescott, Reg. No. 39,335

Amendments to the Drawings:

Figs. 1 and 4 have been amended to extend the lead line for Reference Number 15 to the boundary between the region identified by Reference Number 12 and the region identified by Reference Number 14. The basis for these changes to Figs. 1 and 4 can be found in the Specification on page 7, lines 11-21 and in Fig. 2 of the Drawings. The location of the lead line for Reference Number 15 is correct in Fig. 2.

Replacement Drawings containing these amendments to Figs. 1 and 4 are attached to this paper.